





Drawing No.	*Rev.	Date	Page
BF3H01G-NPD	C	2022/02/24	1/3

APPROVAL SHEET

Part No: **BF3H01G-NPD**

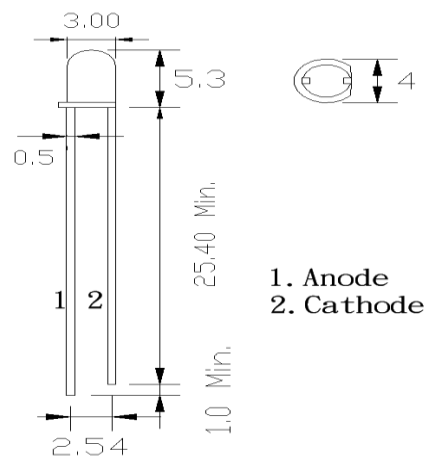
NOTE : Green Part

MAKER			CUSTOMER	
				
R&D	QA	Sales	Checked	Approved
				

Prepared	Checked	Approved
Rachel Lee	Sky Lin	Kenneth Wu

DESCRIPTION:

Device Type : BF3H01G-NPD
 Dice Material : Silicon
 Lens Color : Black
 Lens Dimension : 3 mm



All epoxy resin dimension are in millimeter tolerance is $\pm 0.2\text{mm}$

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Rating.	Unit
Reverse Voltage	V_R	30	V
Power Dissipation	P_C	100	mW
Operating Temperature	T_{opr}	-30 ~ +80	$^\circ\text{C}$
Storage Temperature	T_{str}	-30 ~ +100	$^\circ\text{C}$

Solder DIP (MAX. 5 seconds, 1.6mm from body) Temperature 260°C

Electrical and Optical Characteristics at $T_a=25^\circ\text{C}$

Description	Symbol	Condition	Min.	Typ.	Max.	Unit
Range of Spectral Bandwidth	WP		400		1100	nm
Peak sensitive wavelength	WP			940		nm
Reverse Light Current	I_L	$V_R=5V.E_e=1\text{mW}/\text{cm}^2$		10		μA
Reverse Dark Current	I_D	$V_R=10V.E_e=0\text{mW}/\text{cm}^2$		-	10	nA
Reverse breakdown voltage	V_{BR}	$I_R=100\mu\text{A}.E_e=0\text{mW}/\text{cm}^2$	30			V
Open-Circuit Voltage	V_{OC}	$E_e=5\text{mW}/\text{cm}^2 \lambda_p=940\text{nm}$		0.35		V
Short- Circuit Current	I_{SC}	$E_e=1\text{mW}/\text{cm}^2 \lambda_p=940\text{nm}$		40		μA
Rise Time/ Fall Time	t_r/ t_f	$V_R=10V R_L=1K\Omega$		45/45		ns
Total Capacitance	C_t	$V_R=5V E_e=0\text{mW}/\text{cm}^2$ $f=1\text{MHz}$		15		pF

- Note:
- 1.The lead should be formed up to 5mm from the body of device without forming stress.
 2. Soldering shall be performed after lead forming.
 3. All dimensions are in millimeters.

LED LAMP Technical Data

Typical Optical-Electrical Characteristic Curves

